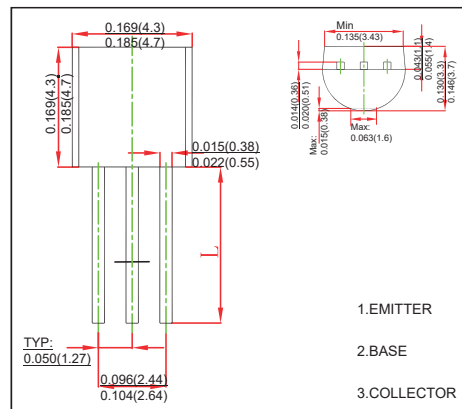


**TO-92 Plastic-Encapsulate Transistors**
**FEATURES**

- Low Saturation Voltage:  $V_{CE(sat)}$
- High DC Current Gain
- TRANSISTOR (PNP)

**MECHANICAL DATA**

- Case style: TO-92 molded plastic
- Mounting position: any


**MAXIMUM RATINGS AND CHARACTERISTICS**

@ 25°C Ambient Temperature (unless otherwise noted)

Parameter	Symbol	Value	Unit
Collector-Base Voltage	<b>VCBO</b>	-20	V
Collector-Emitter Voltage	<b>VCEO</b>	-20	V
Emitter-Base Voltage	<b>VEBO</b>	-6	V
Collector Current -Continuous	<b>IC</b>	-2	A
Collector Power Dissipation	<b>PD</b>	750	mW
Thermal Resistance from Junction to Ambient	<b>RKJA</b>	166	°C /W
Operation Junction and Storage Temperature Range	<b>Tstg</b>	-55~+150	°C

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = -0.1mA, I_E = 0$	-20			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = -10mA, I_B = 0$	-20			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = -0.1mA, I_C = 0$	-6			V
Collector cut-off current	$I_{CBO}$	$V_{CB} = -20V, I_E = 0$			-0.1	
Emitter cut-off current	$I_{EBO}$	$V_{EB} = -6V, I_C = 0$			-0.1	
DC current gain	$h_{FE(1)}$	$V_{CE} = -2V, I_C = -0.1A$	120		400	
	$h_{FE(2)}$	$V_{CE} = -2V, I_C = -2A$	40			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -2A, I_B = -0.1A$			-0.5	V
Base-emitter voltage	$V_{BE}$	$V_{CE} = -2V, I_C = -0.1A$			-0.85	V
Collector output capacitance	$C_{ob}$	$V_{CB} = -10V, I_E = 0, f = 1MHz$		40		pF
Transition frequency	$f_T$	$V_{CE} = -2V, I_C = -0.5A$		120		MHz